



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C		
60V	7.5Ω @ V _{GS} = 5V	0.23A		

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- **Power Management Functions**

SOT363



Top View

Features

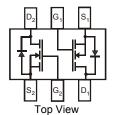
- **Dual N-Channel MOSFET**
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Notes 3 & 4)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208



- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)



Internal Schematic

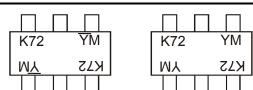
Ordering Information (Note 5)

Part Number	Compliance	Case	Packaging
2N7002DW-7-F	Standard	SOT363	3,000/Tape & Reel
2N7002DWQ-7-F	Automotive	SOT363	3,000/Tape & Reel
2N7002DW-13-F	Standard	SOT363	10,000/Tape & Reel
2N7002DWQ-13-F	Automotive	SOT363	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



K72 = Product Type Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) $\overline{Y}M$ = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Y or \overline{Y} = Year (ex: A = 2013)

M = Month (ex: 9 = September)

Date Code Key

			_	-	_					-				_		
	Year	1998	1999	2000	2001	2002	2003	2004		2011	2012	2013	2014	2015	2016	2017
	Code	J	K	L	M	N	Р	R		Υ	Z	Α	В	C	D	Е
Ī	Month	Jan	Fe	h	Mar	Apr	May	Ju	n	Jul	Aug	Sep	Oc	1	Nov	Dec
	WOTHER	Jan	10		wai	Λþi	iviay	ou		oui	Aug	ОСР	OC		101	Dec
	Code	1	2		3	4	5	6		7	8	9	0		N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	60	V	
Drain-Gate Voltage $R_{GS} \le 1.0 M\Omega$		V_{DGR}	60	V	
Gate-Source Voltage		Continuous	V_{GSS}	±20	V
Gate-Source Voltage	Pulsed		V_{GSS}	±40	V
Continuous Drain Current (Note 7) V _{GS} = 5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$ $T_A = +100^{\circ}C$	I_{D}	0.23 0.18 0.14	Α
Maximum Continuous Body Diode Forward Current	(Note 7)	Is	0.53	Α	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)		I _{DM}	0.8	Α	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
	T _A = +25°C		0.31		
Total Power Dissipation (Note 6)	T _A = +70°C	P_{D}	0.2	W	
	T _A = +100°C		0.12		
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{ heta JA}$	410	°C/W	
	T _A = +25°C		0.4		
Total Power Dissipation (Note 7)	T _A = +70°C	P_{D}	0.25	W	
	T _A = +100°C		0.15		
Thermal Resistance, Junction to Ambient (Note 7)	Steady state	$R_{\theta JA}$	318	°C/W	
Thermal Resistance, Junction to Case (Note 7)	Steady state	$R_{\theta JC}$	135	°C/W	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

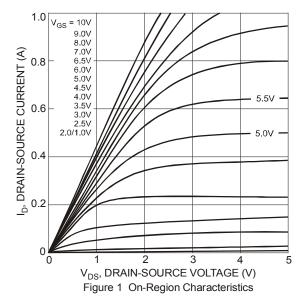
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage		BV_{DSS}	60	70	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ T _C = +25°C @ T _C = +125°C	I _{DSS}		_	1.0 500	μΑ	V _{DS} = 60V, V _{GS} = 0V
Gate-Body Leakage		I _{GSS}	_	_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage		$V_{GS(th)}$	1.0	_	2.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance	@ T _J = +25°C @ T _J = +125°C	R _{DS} (ON)	_	3.2 4.4	7.5 13.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$ $V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current		I _{D(ON)}	0.5	1.0	_	Α	V _{GS} = 10V, V _{DS} = 7.5V
Forward Transconductance		g _{FS}	80	_	_	mS	V _{DS} =10V, I _D = 0.2A
Diode Forward Voltage		V_{SD}	_	0.78	1.5	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance		C _{iss}		22	50	pF), OF),), O),
Output Capacitance		Coss	_	11	25	pF	$V_{DS} = 25V, V_{GS} = 0V$ -f = 1.0MHz
Reverse Transfer Capacitance		Crss	_	2.0	5.0	pF	71 - 1.0IVIDZ
SWITCHING CHARACTERISTICS (Note 9)							
Turn-On Delay Time		t _{D(on)}		7.0	20		$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time		t _{D(off)}	_	11.0	20	ns	$R_L = 150\Omega$, $V_{GEN} = 10V$, $R_{GEN} = 25\Omega$

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Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.





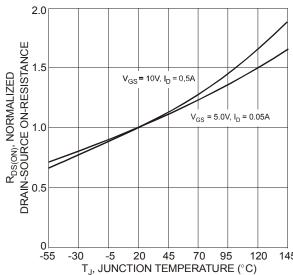
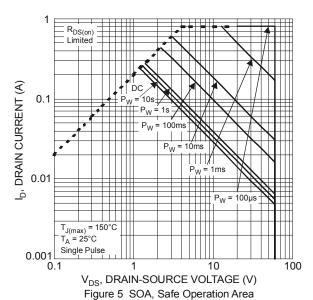
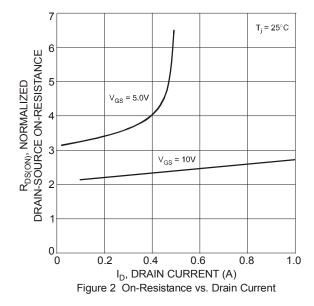
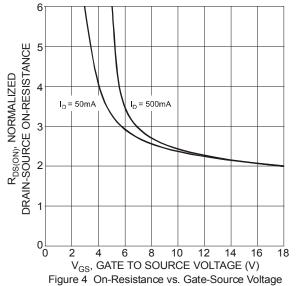


Figure 3 On-Resistance vs. Junction Temperature



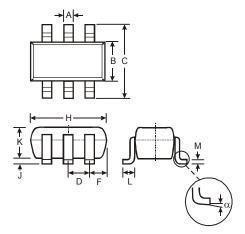






Package Outline Dimensions

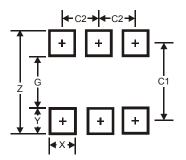
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT363								
Dim	Min	Max						
Α	0.10	0.30						
В	1.15	1.35						
С	2.00	2.20						
D	0.65 Typ							
F	0.40	0.45						
Н	1.80	2.20						
J	0	0.10						
K	0.90	1.00						
L	0.25	0.40						
M	0.10	0.22						
α	0°	8°						
All Di	All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65



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